L Number	Hits	Search Text	DB	Time stamp
1	0	(flash near2 anneal\$3) near10 ((back or	USPAT;	2004/08/21 20:54
		bottom) near5 (substrate or wafer))	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	0004/00/01 01 01
2	0	(USPAT;	2004/08/21 21:31
		near5 (support near2 substrate))	US-PGPUB; EPO; JPO;	
	ļ		DERWENT;	
			IBM TDB	
3	0	anneal\$3 near10 (imping\$3 near5 (support	USPAT;	2004/08/21 21:32
_	-	near2 substrate))	US-PGPUB;	
		·	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
4	0		USPAT;	2004/08/21 21:32
		near2 substrate))	US-PGPUB;	
			EPO; JPO; DERWENT;	· ·
			IBM TDB	
5	o	anneal\$3 same (imping\$3 or though) near5	USPAT;	2004/08/21 21:33
"	Ĭ	(support near2 substrate)	US-PGPUB;	2001,00,21 21.33
		(- pp - s - s - s - s - s - s - s - s -	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
6	10		USPAT;	2004/08/21 21:35
		near5 (support near2 substrate))	US-PGPUB;	
			EPO; JPO;	
			DERWENT; IBM TDB	
7	8	(flash near2 anneal\$3 same ((imping\$3 or	USPAT;	2004/08/21 21:35
'		through) near5 substrate))	US-PGPUB;	2004/00/21 21:33
		onzough, nouzo bubblato,,	EPO; JPO;	
ļ.			DERWENT;	
			IBM_TDB	
-	6192	• • • • • • • • • • • • • • • • • • •	USPAT;	2004/08/20 17:34
		(438/473) or (438/474) or (438/475) or	US-PGPUB;	
		(438/477) or (438/479) or (438/480) or	EPO; JPO;	
		(438/495) or (438/496) or (438/499) or (438/406) or (438/508) or (438/509) or	DERWENT; IBM_TDB	
		(438/514) or (438/787) or (438/788)).CCLS.	100-100	
_	17530		USPAT;	2004/08/21 16:28
		or (silicon near2 quartz) or sof or	US-PGPUB;	
		(silicon near2 foreign)) near3 (substrate	EPO; JPO;	
]		or wafer)	DERWENT;	
	_],,,, ,, ,, ,, ,, ,, ,, ,, ,, ,, ,, ,, ,	IBM_TDB	0001100155 5- 5-
-	0	(((xe adj arc) near2 lamp) same anneal\$3)	USPAT;	2004/08/20 17:48
]		near10 ((support or second silicon or quartz or semiconductor)near2 substrate)	US-PGPUB; EPO; JPO;	
		quartz or semiconductor/hearz substrate)	DERWENT;	
[IBM TDB	
_	0	(((xe adj arc) near2 lamp) same anneal\$3)	USPAT;	2004/08/20 17:48
		same ((support or second silicon or quartz	US-PGPUB;	
		or semiconductor)near2 substrate)	EPO; JPO;	
			DERWENT;	
	_		IBM_TDB	0004/00/00 == :=
-	0	((tare arm)	USPAT;	2004/08/20 17:49
		same ((support or second or silicon or quartz or semiconductor)near2 substrate)	US-PGPUB;	
		quartz or semiconductor/nearz substrate)	EPO; JPO; DERWENT;	
			IBM TDB	
_	0	((soi or (silicon near2 insulator) or soq	USPAT;	2004/08/20 17:49
		or (silicon near2 quartz) or sof or	US-PGPUB;	
		(silicon near2 foreign)) near3 (substrate	EPO; JPO;	
]		or wafer)) and ((((xe adj arc) near2 lamp)	DERWENT;	
		same anneal\$3) and ((support or second or	IBM_TDB	
		silicon or quartz or semiconductor)near2		
L		substrate))	<u> </u>	

and the state of the

			1	1
-	26	and ((support or second or silicon or	USPAT; US-PGPUB;	2004/08/20 17:50
		quartz or semiconductor)near2 substrate)	EPO; JPO; DERWENT;	
-	5	, , , ,	IBM_TDB USPAT;	2004/08/20 17:52
		or heat\$3)) near10 (substrate or (support near2 substrate))	US-PGPUB; EPO; JPO;	
			DERWENT; IBM TDB	
-	54	(((xe adj arc) near2 lamp) same (anneal\$3 or heat\$3))	USPAT; US-PGPUB;	2004/08/20 17:53
			EPO; JPO; DERWENT;	
_	0	((soi or (silicon near2 insulator) or soq	IBM_TDB USPAT;	2004/08/20 17:53
		or (silicon near2 quartz) or sof or (silicon near2 foreign)) near3 (substrate	US-PGPUB; EPO; JPO;	2004/00/20 17:33
		or wafer)) and ((((xe adj arc) near2 lamp)	DERWENT;	
_	206		IBM_TDB USPAT;	2004/08/20 18:03
		or heat\$3))	US-PGPUB; EPO; JPO;	
	_		DERWENT; IBM_TDB	
_	0	or heat\$3))) and ((soi or (silicon near2	USPAT; US-PGPUB;	2004/08/20 17:53
		insulator) or soq or (silicon near2 quartz) or sof or (silicon near2 foreign))	EPO; JPO; DERWENT;	
		near3 (substrate or wafer))) and (((438/149) or (438/311) or (438/458) or	IBM_TDB	
		(438/473) or (438/474) or (438/475) or (438/477) or (438/479) or (438/480) or		
		(438/495) or (438/496) or (438/499) or (438/406) or (438/508) or (438/509) or		
		(438/514) or (438/787) or (438/788)).CCLS.)		
-	34	<pre>(((((xe adj arc) near2 lamp) and (anneal\$3 or heat\$3))) and ((soi or (silicon near2</pre>	USPAT; US-PGPUB;	2004/08/20 17:53
		<pre>insulator) or soq or (silicon near2 quartz) or sof or (silicon near2 foreign))</pre>	EPO; JPO; DERWENT;	
_	10693	near3 (substrate or wafer)) wafer near2 bond\$3	IBM_TDB USPAT;	2004/08/20 18:19
			US-PGPUB; EPO; JPO;	
			DERWENT; IBM TDB	
_	2450	((soi or (silicon near2 insulator) or soq or (silicon near2 quartz) or sof or	USPAT; US-PGPUB;	2004/08/20 18:02
		<pre>(silicon near2 foreign)) near3 (substrate or wafer)) and (wafer near2 bond\$3)</pre>	EPO; JPO; DERWENT;	
_	0		IBM_TDB USPAT;	2004/08/20 18:02
	_	or (silicon near2 quartz) or sof or (silicon near2 foreign)) near3 (substrate	US-PGPUB; EPO; JPO;	
		or wafer)) and (wafer near2 bond\$3)) and ((((xe adj arc) near2 lamp) and (anneal\$3	DERWENT; IBM TDB	
_	3933068	or heat\$3))) anneal\$3 or heat\$3	USPAT;	2004/08/20 18:55
	2223000		US-PGPUB; EPO; JPO;	
			DERWENT; IBM TDB	
_	1808	(anneal\$3 or heat\$3) and (((soi or	USPAT; US-PGPUB;	2004/08/20 18:05
		(silicon near2 insulator) or soq or (silicon near2 quartz) or sof or (silicon	EPO; JPO;	
		<pre>near2 foreign)) near3 (substrate or wafer)) and (wafer near2 bond\$3))</pre>	DERWENT; IBM_TDB	

-	281	((xe adj arc) near2 lamp)	USPAT; US-PGPUB;	2004/08/20 18:03
			EPO; JPO; DERWENT; IBM TDB	
-	0	((anneal\$3 or heat\$3) and (((soi or (silicon near2 insulator) or sog or	USPAT; US-PGPUB;	2004/08/20 18:04
		(silicon near2 quartz) or sof or (silicon near2 foreign)) near3 (substrate or	EPO; JPO; DERWENT;	
		<pre>wafer)) and (wafer near2 bond\$3))) and (((xe adj arc) near2 lamp))</pre>	IBM_TDB	
-	40	((anneal\$3 or heat\$3) and (((soi or (silicon near2 insulator) or soq or	USPAT; US-PGPUB;	2004/08/20 18:29
		(silicon near2 quartz) or sof or (silicon near2 foreign)) near3 (substrate or	EPO; JPO; DERWENT;	
		<pre>wafer)) and (wafer near2 bond\$3))) and (lamp near5 intensit\$3)</pre>	IBM_TDB	
_	15436	wafer near5 bond\$3	USPAT; US-PGPUB;	2004/08/20 18:20
			EPO; JPO; DERWENT; IBM TDB	
_	8537	(wafer near5 bond\$3) and (anneal\$3 or heat\$3)	USPAT; US-PGPUB;	2004/08/20 18:20
			EPO; JPO; DERWENT;	
_	1232	implant\$ near5 (hydrogen near ion\$1)	IBM_TDB USPAT;	2004/08/20 18:27
			US-PGPUB; EPO; JPO;	
	170	(DERWENT; IBM_TDB	2004/00/20 10:57
-	179	<pre>(wafer near5 bond\$3) same (implant\$ near5 (hydrogen near ion\$1))</pre>	USPAT; US-PGPUB; EPO; JPO;	2004/08/20 18:57
			DERWENT; IBM TDB	
-	162	((wafer near5 bond\$3) same (implant\$ near5 (hydrogen near ion\$1))) and ((soi or	USPAT; US-PGPUB;	2004/08/20 18:28
		(silicon near2 insulator) or soq or (silicon near2 quartz) or sof or (silicon	EPO; JPO; DERWENT;	
	150	near2 foreign)) near3 (substrate or wafer))	IBM_TDB	0004/00/00 10 00
	158	<pre>(((wafer near5 bond\$3) same (implant\$ near5 (hydrogen near ion\$1))) and ((soi or (silicon near2 insulator) or sog or</pre>	USPAT; US-PGPUB; EPO; JPO;	2004/08/20 18:28
		(silicon near2 quartz) or sof or (silicon near2 foreign)) near3 (substrate or	DERWENT; IBM TDB	
_	2	<pre>wafer))) and (anneal\$3 or heat\$3) ((((wafer near5 bond\$3) same (implant\$</pre>	USPAT;	2004/08/20 19:38
		<pre>near5 (hydrogen near ion\$1))) and ((soi or (silicon near2 insulator) or soq or</pre>	US-PGPUB; EPO; JPO;	
		<pre>(silicon near2 quartz) or sof or (silicon near2 foreign)) near3 (substrate or wafer))) and (anneal\$3 or heat\$3)) and</pre>	DERWENT; IBM_TDB	
_	37	((((wafer near5 bond\$3) same (implant\$	USPAT;	2004/08/20 18:31
		near5 (hydrogen near ion\$1))) and ((soi or (silicon near2 insulator) or soq or	US-PGPUB; EPO; JPO;	111,10,20 10.01
		(silicon near2 quartz) or sof or (silicon near2 foreign)) near3 (substrate or	DERWENT; IBM_TDB	
_	366	wafer))) and (anneal\$3 or heat\$3)) and lamp	IICDATI.	2004/09/20 10:50
	300	<pre>(wafer near5 bond\$3) and (implant\$ near5 (hydrogen near ion\$1))</pre>	USPAT; US-PGPUB; EPO; JPO;	2004/08/20 18:58
			DERWENT; IBM_TDB	

			.	
-	310	((wafer near5 bond\$3) and (implant\$ near5	USPAT;	2004/08/20 18:58
		(hydrogen near ion\$1))) and ((soi or	US-PGPUB;	
		(silicon near2 insulator) or soq or	EPO; JPO;	
		(silicon near2 quartz) or sof or (silicon	DERWENT;	
		near2 foreign)) near3 (substrate or	IBM_TDB	
	0	<pre>wafer)) (((wafer near5 bond\$3) and (implant\$ near5</pre>	USPAT;	2004/08/20 18:59
-		(hydrogen near ion\$1))) and (soi or	US-PGPUB;	2004/08/20 18.39
		(silicon near2 insulator) or soq or	EPO; JPO;	
		(silicon near2 quartz) or sof or (silicon	DERWENT;	
		near2 foreign)) near3 (substrate or	IBM TDB	
		wafer))) and (((anneal\$3 or heat\$3) same	_	
		lamp) near5 (support near2 substrate))		İ
-	0	(USPAT;	2004/08/20 18:59
		(hydrogen near ion\$1))) and (((anneal\$3 or	US-PGPUB;	
		heat\$3) same lamp) near5 (support near2	EPO; JPO;	
		substrate))	DERWENT;	
	_	///	IBM_TDB USPAT;	2004/08/20 18:59
-	0	(((anneal\$3 or heat\$3) same lamp) near5 (support near2 substrate)) and ((soi or	US-PGPUB;	2004/08/20 18:59
		(silicon near2 insulator) or sog or	EPO; JPO;	
		(silicon near2 quartz) or sof or (silicon	DERWENT;	
		near2 foreign)) near3 (substrate or	IBM TDB	
		wafer))		
-	43	((anneal\$3 or heat\$3) same lamp) near5	USPAT;	2004/08/20 19:01
		(support near2 substrate)	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
•			IBM_TDB	
_	2013	(anneal\$3 or heat\$3) near3 (support near2	USPAT;	2004/08/20 19:02
		substrate)	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
_	71	((anneal\$3 or heat\$3) near3 (support near2	IBM_TDB USPAT;	2004/08/20 19:02
	, +	substrate)) and ((soi or (silicon near2	US-PGPUB;	2004/00/20 19.02
		insulator) or soq or (silicon near2	EPO; JPO;	
		quartz) or sof or (silicon near2 foreign))	DERWENT;	
		near3 (substrate or wafer))	IBM TDB	
-	16	(((anneal\$3 or heat\$3) near3 (support	USPĀT;	2004/08/20 19:03
] .		near2 substrate)) and ((soi or (silicon	US-PGPUB;	
		near2 insulator) or soq or (silicon near2	EPO; JPO;	
		quartz) or sof or (silicon near2 foreign))	DERWENT;	
}		near3 (substrate or wafer))) and (implant\$	IBM_TDB	
_	1	near5 (hydrogen near ion\$1)) "5543636".PN.	USPAT	2004/08/20 19:22
1	4	"5854123" "5882987" "5953622"	USPAT	2004/08/20 19:22
	"	(3634123	USERI	2004/00/20 13:23
	6	("5374564" "5882987" "6146979"	USPAT	2004/08/20 19:24
		"6251754" "6294814" "6323108").PN.	-	,,
-	1	("6376806").PN.	USPAT	2004/08/20 19:35
-	15	("4356384" "4436985" "4707217"	USPAT	2004/08/20 19:36
!		"4755654" "5073698" "5577157"		
]		"5722761" "5756369" "5811327"		
		"5840118" "5892332" "5893952"		
		"5937282" "6080965" "6144171").PN.		
-	335	flash near2 anneal\$3	USPAT;	2004/08/20 19:52
			US-PGPUB;	
			EPO; JPO;	
			DERWENT; IBM TDB	
_	0	(flash near2 anneal\$3) near5 (support	USPAT;	2004/08/20 19:40
		near2 substrate)	US-PGPUB;	2004/00/20 19:40
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	1	(flash near2 anneal\$3) near10 (support	USPAT;	2004/08/20 19:40
		near2 substrate)	US-PGPUB;	
	l		EPO; JPO;	
			DERWENT;	
L			IBM TDB	

-	1	(flash near2 anneal\$3) same (support near2 substrate)	USPAT; US-PGPUB;	2004/08/20 19:40
			EPO; JPO; DERWENT;	
	_		IBM_TDB	0004/00/00 10 44
-	7	(flash near2 anneal\$3) and (support near2 substrate)	USPAT; US-PGPUB;	2004/08/20 19:44
		Substitute	EPO; JPO;	
			DERWENT; IBM TDB	
-	0	(flash near2 anneal\$3) near5 (separt\$5	USPAT;	2004/08/20 19:45
		same substrate)	US-PGPUB; EPO; JPO;	
			DERWENT;	
	0	(61-24	IBM_TDB	2004/00/20 10-45
-	"	(flash near2 anneal\$3) near5 separt\$5	USPAT; US-PGPUB;	2004/08/20 19:45
			EPO; JPO;	
			DERWENT; IBM TDB	
-	0	(flash near2 anneal\$3) near10 separt\$5	USPAT;	2004/08/20 19:46
			US-PGPUB; EPO; JPO;	
			DERWENT;	
_	2	(flash near2 anneal\$3) near10 (through	IBM_TDB USPAT;	2004/08/20 19:47
	-	near5 substrate)	US-PGPUB;	2004/00/20 13:47
			EPO; JPO; DERWENT;	
			IBM TDB	
-	1	(flash near2 anneal\$3) near10 (through near2 substrate)	USPĀT;	2004/08/20 19:48
		Hearz Substrace;	US-PGPUB; EPO; JPO;	
			DERWENT;	
_	1	(flash near2 anneal\$3) near10 (through	IBM_TDB USPAT;	2004/08/20 19:48
		same substrate)	US-PGPUB;	
			EPO; JPO; DERWENT;	
	0.7	1,61	IBM_TDB	
-	27	(flash near2 anneal\$3) near10 (substrate)	USPAT; US-PGPUB;	2004/08/20 19:50
			EPO; JPO;	
			DERWENT; IBM TDB	
-	1	(flash near2 anneal\$3) same (hydrogen	USPĀT;	2004/08/21 16:29
		near2 ion\$1)	US-PGPUB; EPO; JPO;	
			DERWENT;	
_	18	flash near2 anneal\$3 and ((soi or (silicon	IBM_TDB USPAT;	2004/08/20 19:55
		near2 insulator) or soq or (silicon near2	US-PGPUB;	
		<pre>quartz) or sof or (silicon near2 foreign)) near3 (substrate or wafer))</pre>	EPO; JPO; DERWENT;	
			IBM_TDB	
-	42016	flash near2 anneal\$3 or ((xe adj arc) near2 lamp) or xenon	USPAT; US-PGPUB;	2004/08/21 18:41
		Tamp, or nonon	EPO; JPO;	
	i		DERWENT; IBM TDB	
	20	(flash near2 anneal\$3 or ((xe adj arc)	USPAT;	2004/08/20 19:56
		near2 lamp) or xenon) same ((soi or (silicon near2 insulator) or soq or	US-PGPUB; EPO; JPO;	
		(silicon near2 quartz) or sof or (silicon	DERWENT;	
		<pre>near2 foreign)) near3 (substrate or wafer))</pre>	IBM_TDB	
-	41728	((xe adj arc) near2 lamp) or xenon	USPAT;	2004/08/21 16:30
			US-PGPUB; EPO; JPO;	
			DERWENT;	İ
		<u> </u>	IBM_TDB	

-	40914	(soi or (silicon near2 insulator) or soq	USPAT;	2004/08/21 16:28
		or (silicon near2 quartz) or sof or	US-PGPUB;	
		(silicon near2 foreign))	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
_	869	1 ' ''	USPAT;	2004/08/21 16:28
		((soi or (silicon near2 insulator) or soq	US-PGPUB;	
		or (silicon near2 quartz) or sof or	EPO; JPO;	
		(silicon near2 foreign)))	DERWENT;	
			IBM_TDB	
-	1422	(hydrogen near2 ion\$1) near5 implant\$5	USPAT;	2004/08/21 16:29
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	47	'	USPĀT;	2004/08/21 16:29
		((soi or (silicon near2 insulator) or soq	US-PGPUB;	
•		or (silicon near2 quartz) or sof or	EPO; JPO;	
		(silicon near2 foreign)))) and (DERWENT;	
		(hydrogen near2 ion\$1) near5 implant\$5)	IBM_TDB	
-	19527	((xe adj arc) near2 lamp) or xenon near3	USPAT;	2004/08/21 16:30
		lamp	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	330		USPAT;	2004/08/21 16:30
		lamp) and ((soi or (silicon near2	US-PGPUB;	
		insulator) or soq or (silicon near2	EPO; JPO;	
		quartz) or sof or (silicon near2 foreign))	DERWENT;	1
)	IBM_TDB	
-	13	' ' ' ' ' ' ' ' ' ' ' ' ' ' ' ' ' ' '	USPAT;	2004/08/21 16:31
		near3 lamp) and ((soi or (silicon near2	US-PGPUB;	
		insulator) or soq or (silicon near2	EPO; JPO;	
		quartz) or sof or (silicon near2 foreign))	DERWENT;	
)) and ((hydrogen near2 ion\$1) near5	IBM_TDB	
		implant\$5)		
-	35	(flash near2 anneal\$3) near5 (substrate or	USPAT;	2004/08/21 20:53
		wafer)	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
	1		IBM TDB	